

**SPECIFICATION AMENDMENTS**

Please amend the specification as follows:

Change the paragraph beginning at page 5, line 26, to read as follows:

B2

-- The manufacturing process in which the present invention is incorporated begins with the faceplate 150 being disposed in the plasma sputter chamber 152 with the phosphors 151 exposed. The plasma sputter chamber 152 ~~150~~ is pumped down to about  $10^{-7}$  to  $10^{-8}$  torr and a plasma 156 of low atomic weight gasses, such as hydrogen or helium, is formed. The faceplate 150 is then scrubbed by plasma sputtering of ions or electrons 158 by being subjected to a respective voltage of -10 to -1000 V ~~mV~~ or +10 to +1000 V ~~mV~~ for about 1 to 60 minutes. --